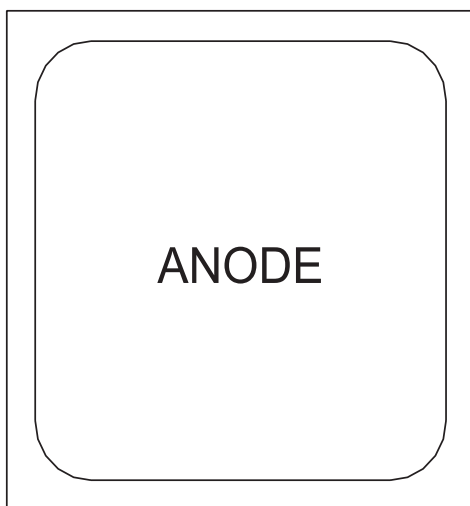


PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	98 x 98 MILS
Die Thickness	10.6 MILS
Anode Bonding Pad Area	82.5 x 82.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

1,170

PRINCIPAL DEVICE TYPES

CR6AF1GPP Series

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Hauppauge, NY 11788 USA
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R1 (1-August 2002)



The Typical Electrical Characteristics data
for this chip is currently being revised.

For the latest updated data for this Chip Process,
please visit our website at:

www.centrasemi.com/chip